

JAN Qualified N-Channel 60-V (D-S) MOSFETs

PRODUCT SUMMARY							
V _{(BR)DSS} Min (V)	$r_{DS(on)}$ Max (Ω)	V _{GS(th)} (V)	I _D (A)				
60	3 @ V _{GS} = 10 V	0.8 to 2	0.99				

FEATURES

Military Qualified

Low On-Resistance: 1.3 Ω

Low Threshold: 1.7 V

Low Input Capacitance: 35 pF • Easily Driven Without Buffer

• Fast Switching Speed: 8 ns

Low Input and Output Leakage

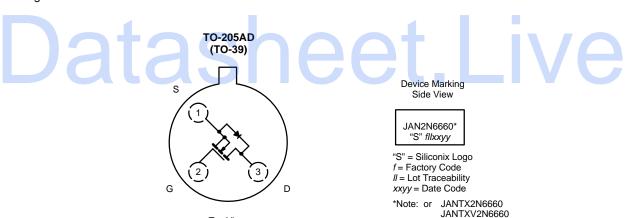
BENEFITS

- Guaranteed Reliability
- Low Offset Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Error Voltage

Top View

APPLICATIONS

- Military Applications
- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)								
Parameter		Symbol	Limit	Unit				
Drain-Source Voltage		V _{DS}	60	V				
Gate-Source Voltage		V _{GS}	±20					
Continuous Drain Current (T _J = 150°C)	T _C = 25°C		0.99					
	T _C = 100°C	l _D	0.62	А				
Pulsed Drain Current ^a		I _{DM}	3					
Power Dissipation	$T_C = 25^{\circ}C$		6.25	10/				
	T _A = 25°C	P _D	0.725	W				
Thermal Resistance, Junction-to-Ambient ^b		R _{thJA}	170	2011				
Thermal Resistance, Junction-to-Case		R _{thJC}	20	°C/W				
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C				

Pulse width limited by maximum junction temperature.

b. Not required by Military Spec.

2N6660JAN/JANTX/JANTXV

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SPECIFICATIONS ²								
	Symbol			Limits				
Parameter		Test Conditions	Min	Typb	Max	Unit		
Static			•		•			
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 10 \mu\text{A}$	60	75				
Gate-Threshold Voltage		$V_{DS} = V_{GS}$, $I_D = 1 \text{ mA}$	0.8	1.7	2	V		
	V _{GS(th)}	$T_C = -55^{\circ}C$			2.5	V		
		T _C = 125°C	0.3					
Gate-Body Leakage	Lea	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA		
	I _{GSS}	T _C = 125°C			±500			
Zoro Coto Voltago Proin Current	1	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1			
Zero Gate Voltage Drain Current	I _{DSS}	T _C = 125°C			100	μΑ		
On-State Drain Current ^c	I _{D(on)}	V _{DS} = 10 V, V _{GS} = 10 V		2		Α		
Drain-Source On-Resistance ^c		$V_{GS} = 5 \text{ V}, I_D = 0.3 \text{ A}$		2	5			
	r _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 1 \text{ A}$		1.3	3	Ω		
		T _C = 125°C		2.4	5.6]		
Forward Transconductance ^c	9 _{fs}	$V_{DS} = 7.5 \text{ V}, I_{D} = 0.525 \text{ A}$	170	350		mS		
Diode Forward Voltage	V _{SD}	I _S = 0.99 A, V _{GS} = 0 V	0.7	0.8	1.6	V		
Dynamic			•		•			
Input Capacitance	C _{iss}			35	50	pF		
Output Capacitance	C _{oss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$ $f = 1 \text{ MHz}$		25	40			
Reverse Transfer Capacitance	C _{rss}			7	10			
Drain-Source Capacitance	C _{ds}			30				
Switching ^d								
Turn-On Time	t _{ON}	V_{DD} = 25 V, R_L = 23 Ω I_D \cong 1 A, V_{GEN} = 10 V R_G = 25 Ω		8	10	ns		
Turn-Off Time	t _{OFF}			8.5	10			

Notes a. $T_A = 25\,^{\circ}\text{C}$ unless otherwise noted. b. For DESIGN AID ONLY, not subject to production testing. Pulsa test: PW $\leq 300\,\mu\text{s}$ duty cycle $\leq 2\%$.

Pulse test: PW \leq 300 μ s duty cycle \leq 2%. Switching time is essentially independent of operating temperature. For typical characteristics curves see the 2N6659/2N6660, VQ1004J/P data sheet.

VNDQ06



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